



제 30회 한국반도체학술대회

The 30th Korean Conference on Semiconductors

2023년 2월 13일(월)~ 15일(수) | 강원도 하이원리조트(그랜드호텔 컨벤션타워)

2023년 2월 14일(화), 09:00-10:45

Room A (에메랄드 1, 5층)

D. Thin Film Process Technology 분과

[TA1-D] Metallic Films

좌장: 김성근 책임연구원(한국과학기술연구원), 엄태용 임연구원(한국화학연구원)

<p>TA1-D-1 09:00-09:30 [초청]</p>	<p>반도체 소자에서 구리 범프와 절연 고분자의 하이브리드 분당 심영주, 김한글, 황경석, 김주영 울산과학기술원 신소재공학과</p>
<p>TA1-D-2 09:30-09:45</p>	<p>Molybdenum Carbide Thin Films Deposited by Thermal Atomic Layer Deposition Method under Thermal Decomposition of Mo Precursor Min-Ji Ha, Jeong-Hun Choi, and Ji-Hoon Ahn <i>Department of Materials Science and Chemical Engineering, Hanyang University</i></p>
<p>TA1-D-3 09:45-10:00</p>	<p>Composition and Work Function Tuning of Plasma-enhanced Atomic-layer Deposited MoC_xN_y Films Ji Sang Ahn, Wangu Kang, and Jeong Hwan Han <i>Department of Materials Science and Engineering, Seoul National University of Science and Technology</i></p>
<p>TA1-D-4 10:00-10:15</p>	<p>Modified Atomic Layer Deposition of Low-resistivity Molybdenum Carbide and Nitride Electrode for Next Generation DRAM Capacitor Wangu Kang, Ji Sang Ahn, and Jeong Hwan Han <i>Department of Materials Science and Engineering, Seoul National University of Science and Technology</i></p>
<p>TA1-D-5 10:15-10:30</p>	<p>Atomic Layer Etching of Ruthenium Films with Organic Precursor Jeongbin Lee, Jung-Tae Kim, and Woo-Hee Kim <i>Department of Materials Science and Chemical Engineering, Hanyang University</i></p>
<p>TA1-D-6 10:30-10:45</p>	<p>Growth Characteristics of Atomic Layer Deposited Iridium Thin Films with TICP and Oxygen Hong Keun Chung^{1,2}, Tae Joo Park², and Seong Keun Kim^{1,3} ¹Electronic Materials Research Center, KIST, ²Department of Materials Science and Chemical Engineering, Hanyang University, ³KU-KIST Graduate School of Converging Science and Technology, Korea University</p>